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(54) SILICA-BASED FILM, COMPOSITION FOR FORMING SILICA-BASED FILM, METHOD OF PREPARING SILICA-BASED FILM, AND ELECTRONIC COMPONENT

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a composition for forming a silica-based film whereby a silica-based film can be readily prepared with sufficient mechanical strength, a sufficiently low dielectric property, high adhesion to a silicon wafer, and high electrical reliability in some cases. SOLUTION: The composition for forming the film comprises (a) a siloxane resin obtained by hydrolyzing and condensing a compound expressed by the following general formula (1) (where, R1 represents H or F or a group containing B, N, Al, P, Si, Ge, or Ti, or an organic group having a carbon number of 1 to 20 that may be the same or different, X represents a hydrolyzable group which may be the same or different, and n represents an integer of 0, 1, or 2), and (b) a carbodiimide.

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